

FEATURES

- Near Infrared Reduced Footprint Photodiode
- Photosensitive Active Area: 0.6 mm x 0.6 mm
- High Sensitivity: 0.65 A/W ($\lambda = 850$ nm)
- Wide Operating Temperature: -40°C to +110°C
- Ideal for High Volume Laser Monitoring Applications
- RoHS and REACH Compliant

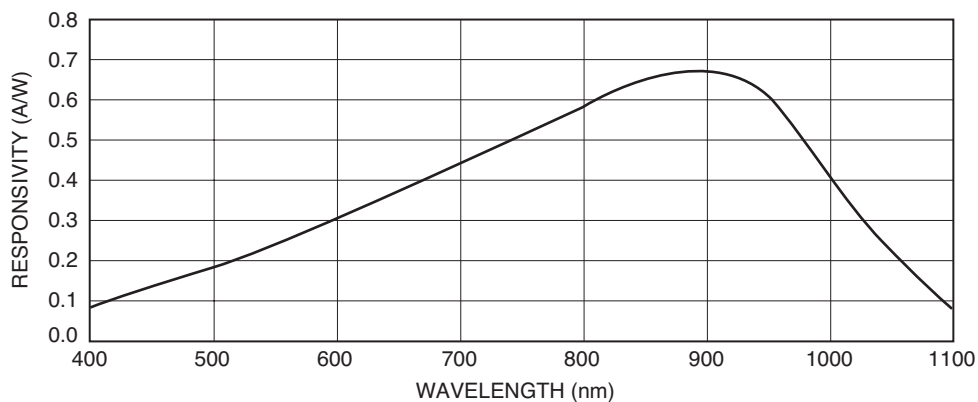
Electro-Optical Characteristics at 25°C

Parameters	Test Conditions	Min	Typ	Max	Units
Active Area			0.36		mm ²
Responsivity	(see graph on next page)		0.65		A/W
Dark Current, I_{dr}	$V_r = 3$ V		0.05	0.3	nA
Shunt Resistance	$V_R = 10$ mV	200	1000		M Ω
Reverse Breakdown Voltage, V_R	$I_R = 10$ μ A	25			Volts
Capacitance, C	$V_R = 0$ V			8	pF
Rise Time	$V_R = 10$ V		8	15	nsec

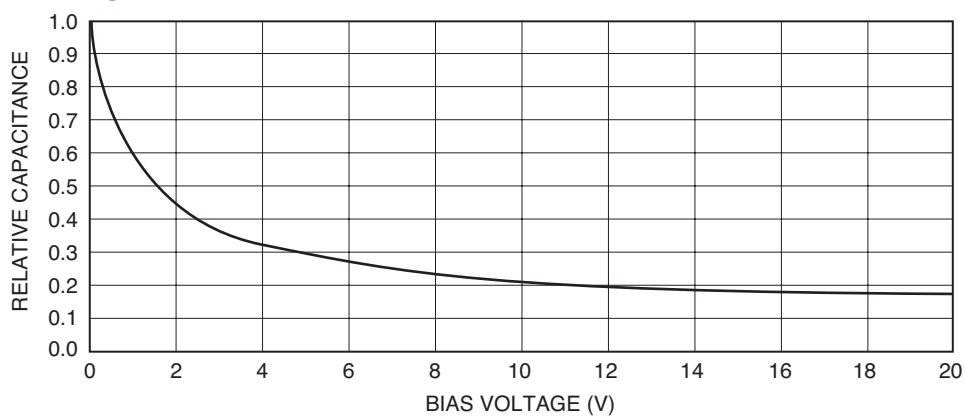
Thermal Parameters

Parameters	Units
Storage and Operating Temperature Range	-40°C to 110°C
Maximum Junction Temperature	110°C

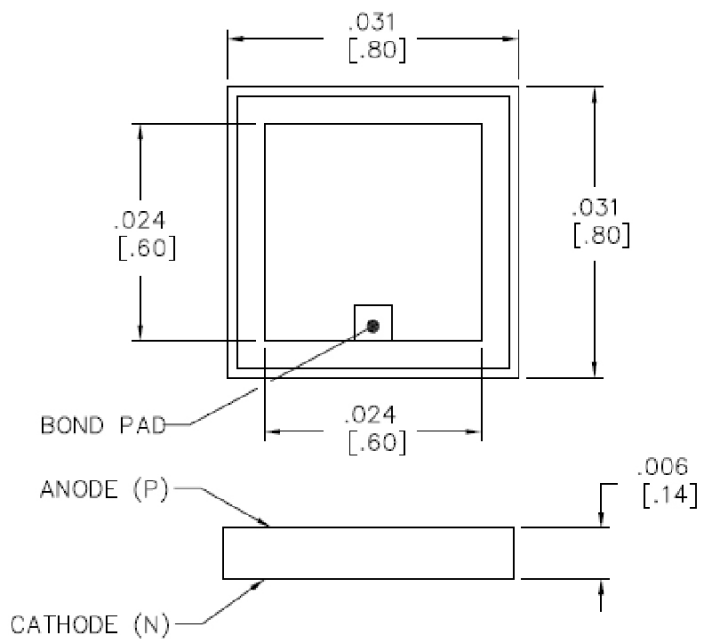
Typical Spectral Response



Capacitance vs Bias Voltage



Package Dimensions



Specifications are subject to change without prior notice.